

Turbo 2 ultrafast - high voltage rectifier

Main product characteristics

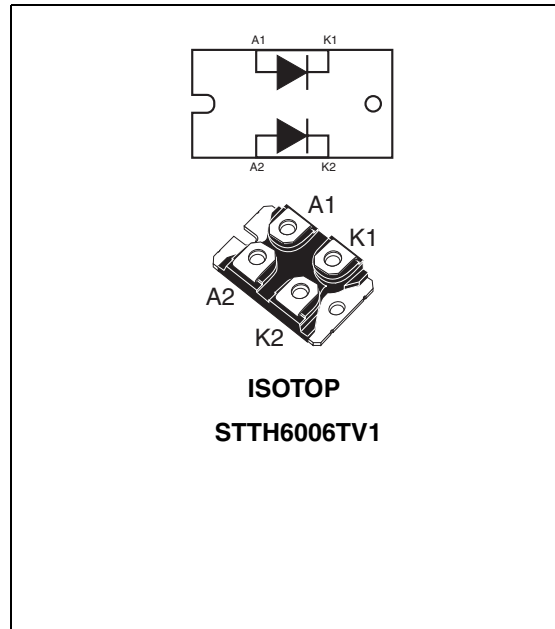
$I_{F(AV)}$	2 x 30 A
V_{RRM}	600 V
T_j	150° C
V_F (typ)	1.1 V
t_{rr} (max)	50 ns

Features and benefits

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces conduction and switching losses
- Insulated voltage: 2500 V_{RMS}
- Typical package capacitance: 45 pF

Description

The STTH6006TV1 uses ST Turbo2 600V technology. This device is specially suited for use in switching power supplies, and industrial applications such as rectification and PFC boost diode.



Order codes

Part Number	Marking
STTH6006TV1	STTH6006TV1

Table 1. Absolute ratings (limiting values per diode at 25° C, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward current		100	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	Per diode $T_c = 70^\circ \text{C}$	30	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	210	A
T_{stg}	Storage temperature range		-55 to + 150	°C
T_j	Maximum operating junction temperature ⁽¹⁾		150	°C

1. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

1 Characteristics

Table 2. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6	° C/W
		Total	0.85	
$R_{th(c)}$	Coupling		0.1	

When the diodes are used simultaneously:

$$\Delta T_{j(\text{diode1})} = P_{(\text{diode1})} \times R_{th(j-c)} \text{ (per diode)} + P_{(\text{diode2})} \times R_{th(c)}$$

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ \text{C}$	$V_R = V_{RRM}$			25	μA
		$T_j = 125^\circ \text{C}$			80	800	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ \text{C}$	$I_F = 30 \text{ A}$			1.85	V
		$T_j = 150^\circ \text{C}$			1.10	1.40	

1. Pulse test: $t_p = 5 \text{ ms}$, $\delta < 2 \%$

2. Pulse test: $t_p = 380 \mu\text{s}$, $\delta < 2 \%$

To evaluate the conduction losses use the following equation:

$$P = 1.07 \times I_{F(AV)} + 0.011 I_F^2(\text{RMS})$$

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 0.5 \text{ A}$, $I_{rr} = 0.25 \text{ A}$, $I_R = 1 \text{ A}$, $T_j = 25^\circ \text{C}$			50	ns
		$I_F = 1 \text{ A}$, $dI_F/dt = -50 \text{ A}/\mu\text{s}$, $V_R = 30 \text{ V}$, $T_j = 25^\circ \text{C}$		50	70	
I_{RM}	Reverse recovery current	$I_F = 30 \text{ A}$, $dI_F/dt = -100 \text{ A}/\mu\text{s}$, $V_R = 400 \text{ V}$, $T_j = 125^\circ \text{C}$		8	11	
t_{fr}	Forward recovery time	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$, $T_j = 25^\circ \text{C}$			500	ns
V_{FP}	Forward recovery voltage	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$, $T_j = 25^\circ \text{C}$		2.5		V

Figure 1. Conduction losses versus average current

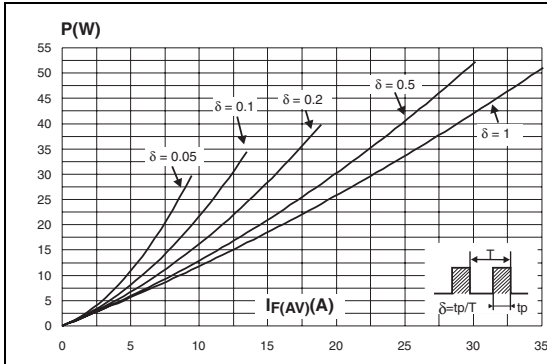


Figure 2. Forward voltage drop versus forward current

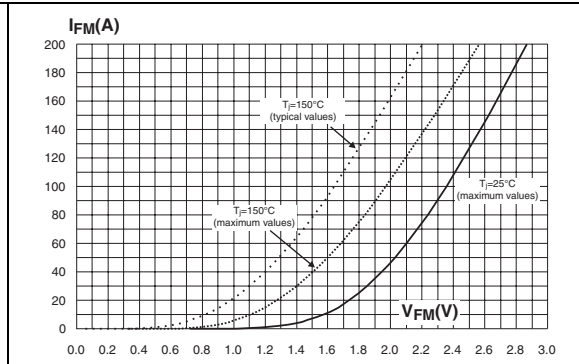


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

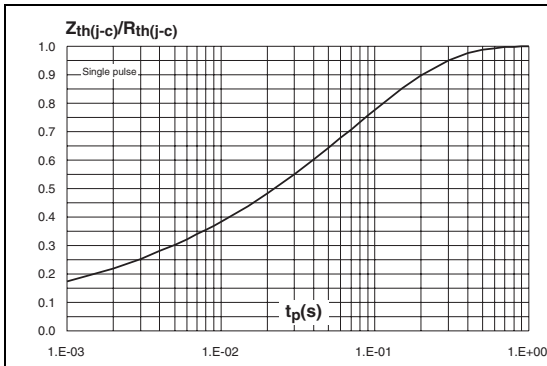


Figure 4. Peak reverse recovery current versus dIF/dt (typical values)

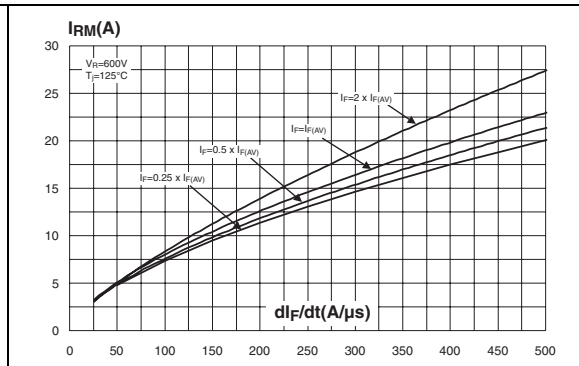


Figure 5. Reverse recovery time versus dIF/dt (typical values)

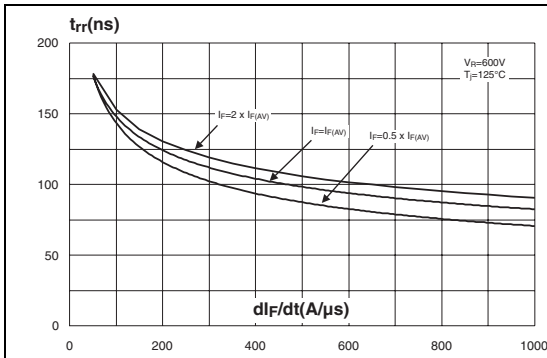


Figure 6. Reverse recovery charges versus dIF/dt (typical values)

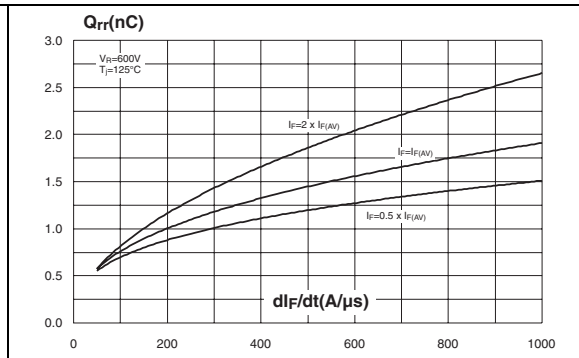


Figure 7. Softness factor versus di_F/dt (typical values)

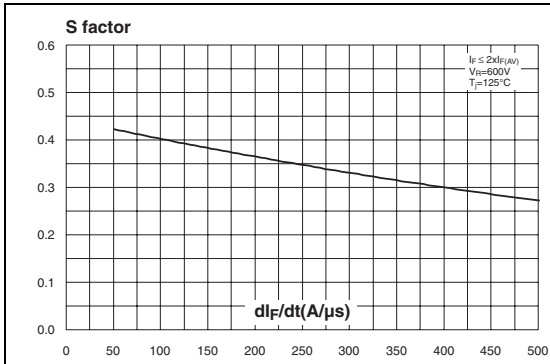


Figure 8. Relative variations of dynamic parameters versus junction temperature

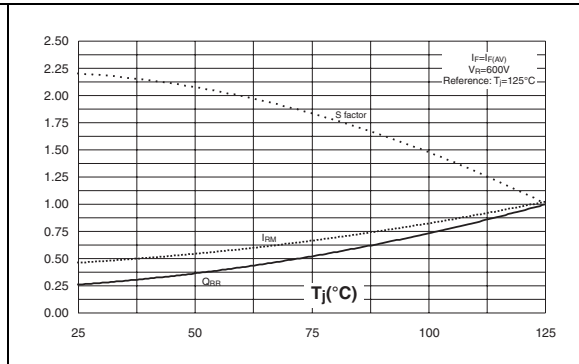


Figure 9. Transient peak forward voltage versus di_F/dt (typical values)

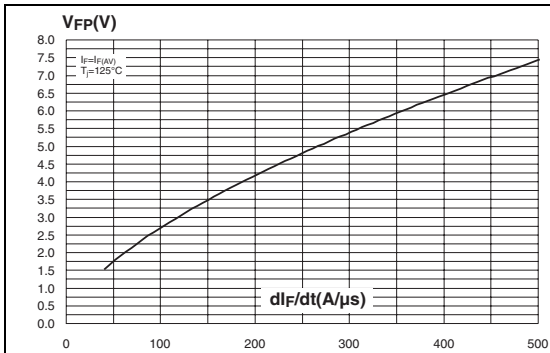


Figure 10. Forward recovery time versus di_F/dt (typical values)

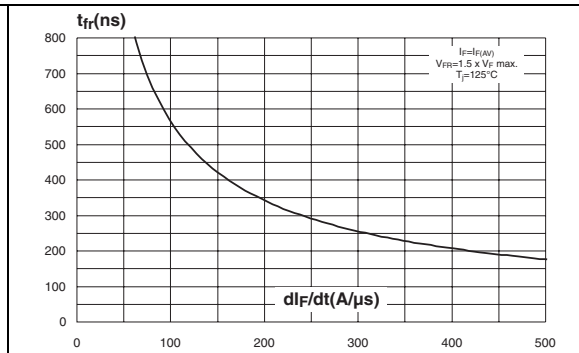
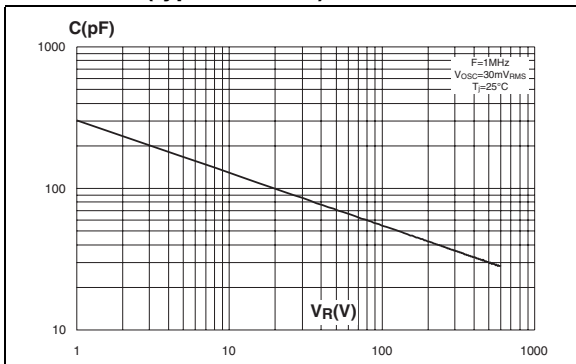


Figure 11. Junction capacitance versus reverse voltage applied (typical values)



2 Package mechanical data

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Table 5. ISOTOP dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH6006TV1	STTH6006TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Date	Revision	Description of Changes
18-May-2006	1	First issue.

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